

Silicon NPN Power Transistor

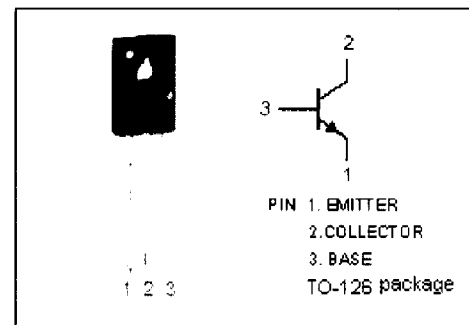
BD723

DESCRIPTION

- DC Current Gain-
: $h_{FE} = 40 @ I_C = 0.5A$
- Collector-Emitter Breakdown Voltage -
: $V_{(BR)CEO} = 100V(\text{Min})$
- Complement to type BD724

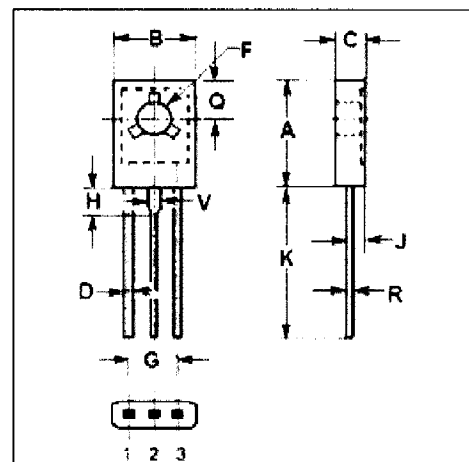
APPLICATIONS

- Designed for use in audio output and general purpose amplifier applications.



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	100	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	4	A
I_{CM}	Collector Current-Peak	7	A
I_B	Base Current-Continuous	1	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	30	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$



DIM	mm	
	MIN	MAX
A	10.70	10.90
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	16.10	16.30
O	3.70	3.90
R	0.40	0.60
V	1.17	1.37

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	3.5	$^\circ\text{C/W}$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	100	$^\circ\text{C/W}$

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ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 30\text{mA}; I_B = 0$	100			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 2\text{A}; I_B = 0.2\text{A}$			1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = 2\text{A}; V_{CE} = 4\text{V}$			1.4	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 100\text{V}; I_E = 0$			50	μA
		$V_{CB} = 50\text{V}; I_E = 0; T_C = 150^\circ\text{C}$			1	mA
I_{CEO}	Collector Cutoff Current	$V_{CE} = 50\text{V}; I_B = 0$			0.1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 5\text{V}; I_C = 0$			0.2	mA
h_{FE-1}	DC Current Gain	$I_C = 0.5\text{A}; V_{CE} = 4\text{V}$	40			
h_{FE-2}	DC Current Gain	$I_C = 2\text{A}; V_{CE} = 4\text{V}$	20			
f_T	Current-Gain—Bandwidth Product	$I_C = 0.5\text{A}; V_{CE} = 4\text{V}$	3			MHz

Switching Times

t_{on}	Turn-On time	$I_C = 1\text{A}; I_{B1} = -I_{B2} = 0.1\text{A}; V_{CC} = 20\text{V}$		0.3		μs
t_{off}	Turn-Off time			1.5		μs